



INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)			ATTY DOCKET NO.	SERIAL NO.		
			ITL.1027US (P16711)	10/696,204		
			APPLICANT(S): YING ZHOU, ET AL.			
FILING DATE: October 29, 2003	GROUP ART UNIT: -2812 2823					
<b>U.S. PATENT DOCUMENTS</b>						
*EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.						
B.						
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E.						
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<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES      NO
J.						
K.						
L.						
M.						
N.						
O.						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
<i>ML</i>	P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, <a href="http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf">http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf</a>				
<i>ML</i>	Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at <a href="http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf">http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf</a>				
	R.					
	S.					
	T.					
EXAMINER <i>Michelle Obriada</i>			DATE CONSIDERED	9/27/04		

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.